General Description

The WSD3020DN is the highest performance trench Dual N-Ch MOSFET with extreme high cell density,which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD3020DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

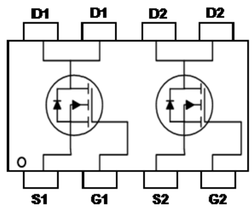
Product Summery

BVDSS	RDSON	ID
30V	17mΩ	21A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C$=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	21	A
$I_D@T_C$=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	13	A
$I_D@T_A$=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	7.5	A
$I_D@T_A$=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	6.0	A
I_{DM}	Pulsed Drain Current[2]	25	A
EAS	Single Pulse Avalanche Energy[3]	15	mJ
I_{AS}	Avalanche Current	17	A
$P_D@T_C$=25℃	Total Power Dissipation[4]	14	W
$P_D@T_A$=25℃	Total Power Dissipation[4]	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	70	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	8.5	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.0232	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=7.5A	---	17	19	mΩ
		V_{GS}=4.5V , I_D=6.8A	---	20	25	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.08	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=7.5A	---	22	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.2	3.0	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=7.5A	---	5.9	8	nC
Q_{gs}	Gate-Source Charge		---	2.1	2.9	
Q_{gd}	Gate-Drain Charge		---	2.0	3.2	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GEN}=10V , R_G=6Ω I_D=1A ,R_L=15Ω	---	14	19	ns
T_r	Rise Time		---	10	17	
$T_{d(off)}$	Turn-Off Delay Time		---	20	62	
T_f	Fall Time		---	8	12	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	526	---	pF
C_{oss}	Output Capacitance		---	76	---	
C_{rss}	Reverse Transfer Capacitance		---	62	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=7.5A	15	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	21	A
I_{SM}	Pulsed Source Current[2,6]		---	---	25	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=7.5A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	I_F=7.5A,dI/dt=100A/µs,T_J=25℃	---	12	---	nS
Q_{rr}	Reverse Recovery Charge		---	3	---	nC

Note :
1.The data tested by surface mounted on a 1 $inch^2$ FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=7.5A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

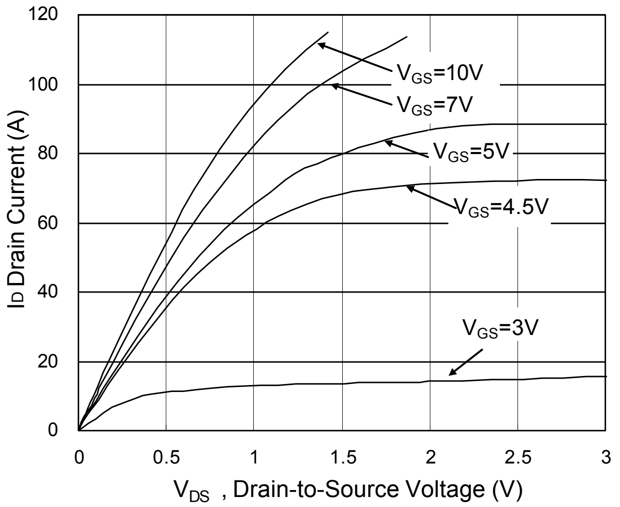


Fig.1 Typical Output Characteristics

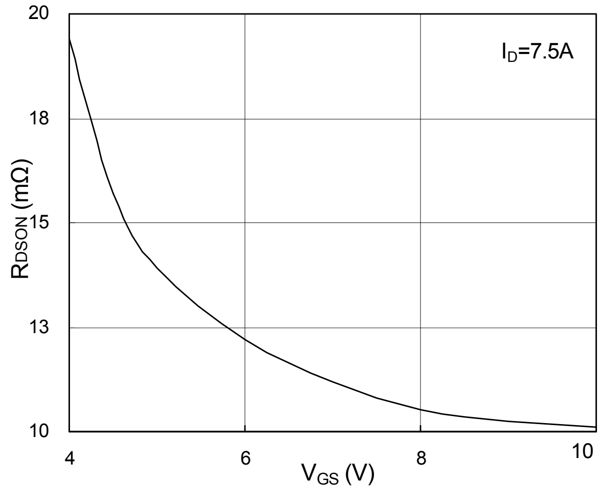


Fig.2 On-Resistance vs. G-S Voltage

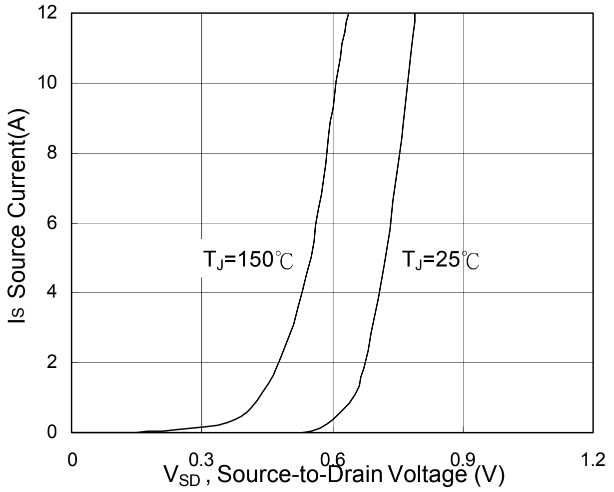


Fig.3 Forward Characteristics of Reverse

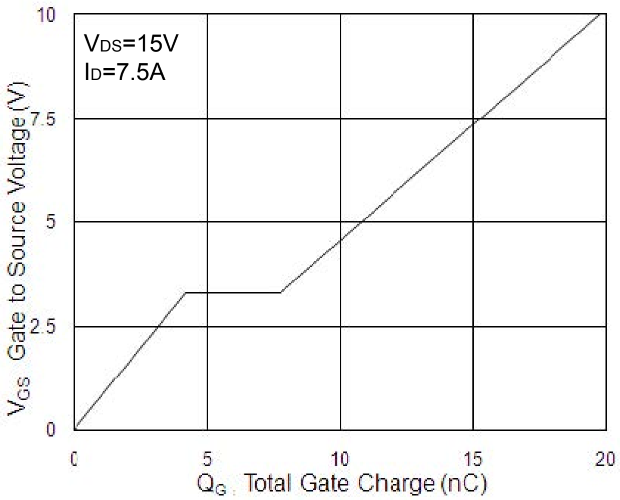


Fig.4 Gate-charge Characteristics

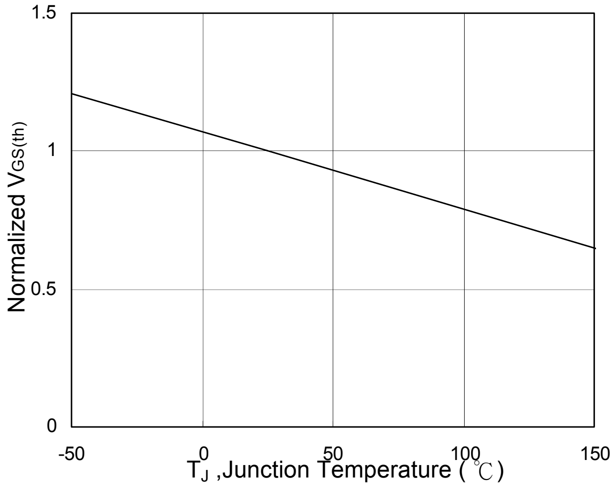


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

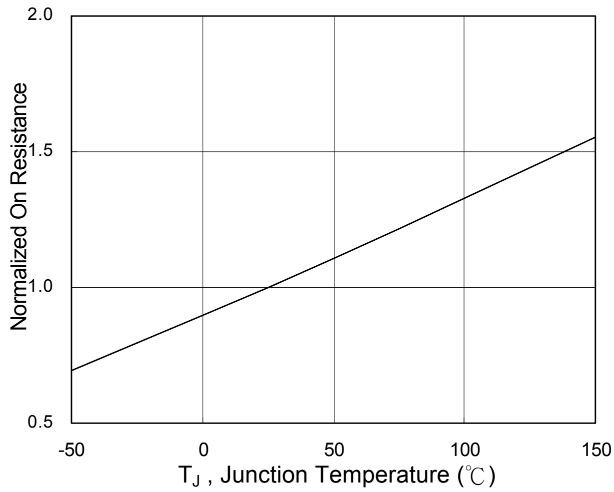


Fig.6 Normalized R_{DSON} vs. T_J

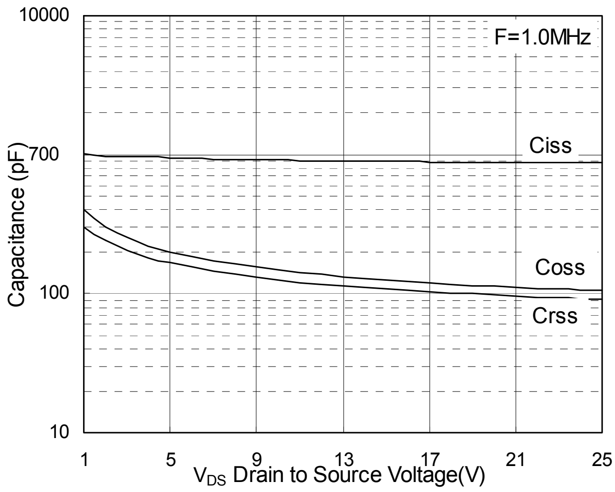


Fig.7 Capacitance

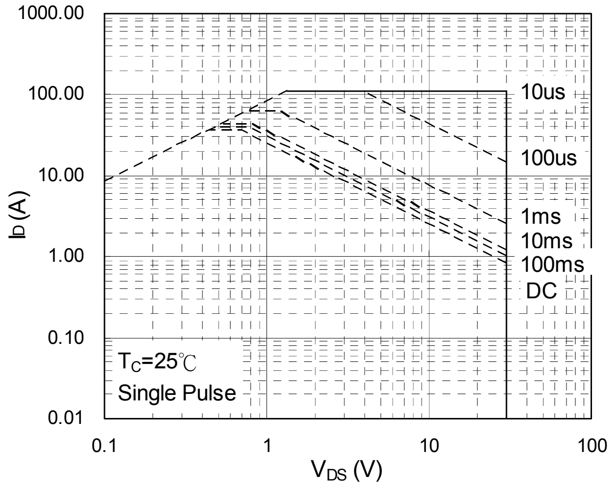


Fig.8 Safe Operating Area

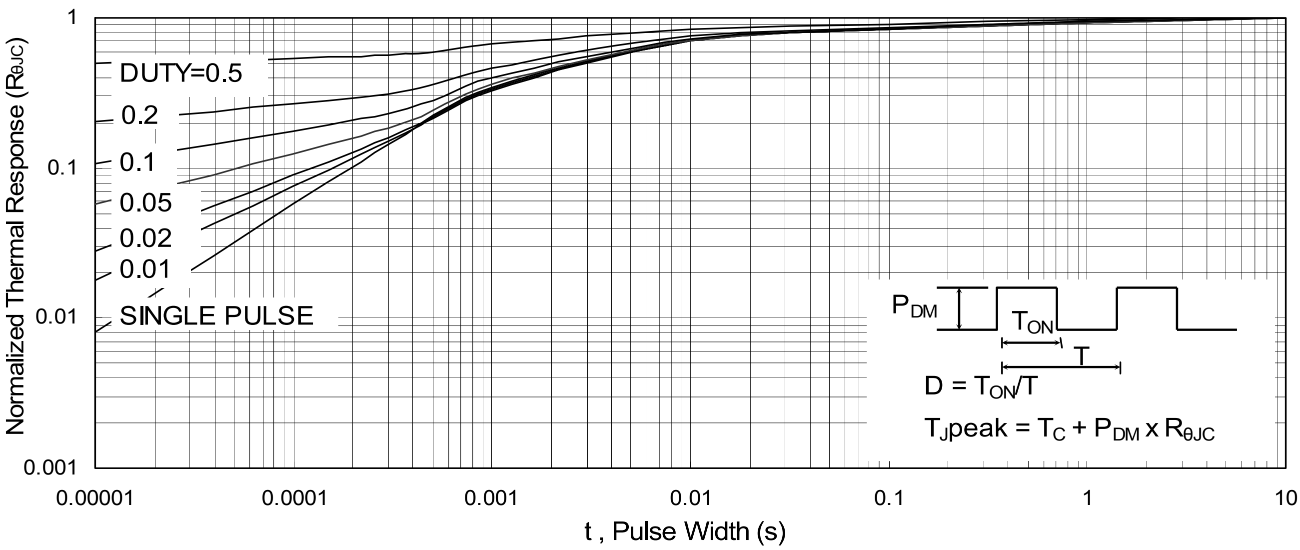


Fig.9 Normalized Maximum Transient Thermal Impedance

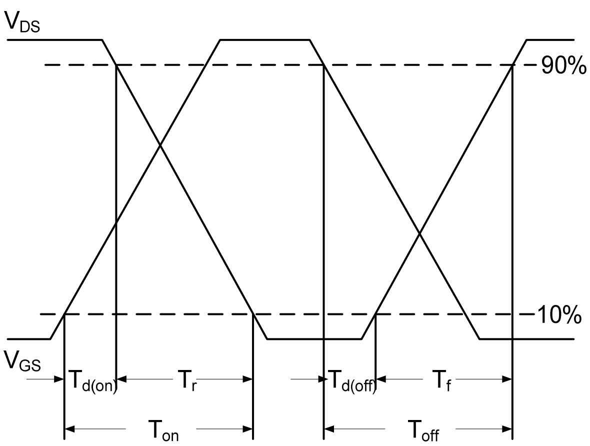


Fig.10 Switching Time Waveform

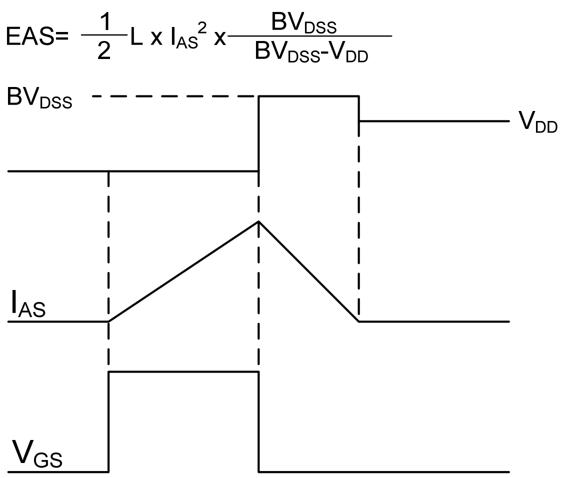


Fig.11 Unclamped Inductive Switching Waveform

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